

SANYO Semiconductors DATA SHEET

LB11620T — Brushless Motor Driver

Overview

The LB11620T is a direct PWM drive predriver IC that is optimal for three-phase power brushless motors. A motor driver circuit with the desired output capability (voltage and current) can be implemented by adding discrete transistors or other power devices to the outputs of this IC. Since the LB11620T is provided in a miniature package, it is also appropriate for use with miniature motors as well.

Features

- Three-phase bipolar drive
- Direct PWM drive (input of either a control voltage or a variable-duty PWM signal)
- Built-in forward/reverse switching circuit
- Full complement of protection circuits (current limiter, low-voltage, and automatic recovery lock (motor constraint) protection circuits)
- Selectable Hall sensor signal pulse output

Specifications

Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions Ratings		Unit
Supply voltage 1	V _{CC} max	V _{CC} pin	18	V
Output current	I _O max	UL, VL, WL, UH, VH, WH pins	30	mA
Allowable power dissipation	Pd max	*Mounted on a circuit board.	0.8	W
Operating temperature	Topr		-20 to +100	°C
Storage temperature	Tstg		-55 to +150	°C

^{*} Mounted on a circuit board: 114.3mm×76.1mm×1.6mm, glass epoxy board.

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Recommended Operating Ranges at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage range 1-1	V _{CC} 1-1	V _{CC} pin	8 to 17	٧
Supply voltage range 1-2	V _{CC} 1-2	V_{CC} pin, with V_{CC} shorted to VREG	4.5 to 5.5	٧
Output current	IO	UL, VL, WL, UH, VH, WH pins	25	mA
5 V constant voltage output current	IREG		-30	mA
HP pin voltage	VHP		0 to 17	V
HP pin output current	IHP		0 to 15	mA
RD pin voltage	VRD		0 to 17	V
RD pin output current	IRD		0 to 15	mA

Electrical Characteristics at $Ta=25^{\circ}C,\ V_{CC}=12V$

Description	O. made al	Conditions			Unit			
Parameter	Symbol		min	typ	max	Uniit		
Supply voltage 1	I _{CC} 1			12	16	mA		
5V constant voltage output (VREG pin)								
Output voltage	VREG		4.7	5.0	5.3	V		
Line regulation	ΔVREG1	V _{CC} = 8 to 17V		40	100	mV		
Load regulation	∆VREG2	I _O = -5 to -20mA		10	30	mV		
Temperature coefficient	ΔVREG3	Design target		0		mV/°C		
Low-voltage protection circuit (VREC	G pin)		•	•				
Operating voltage	VSDL		3.5	3.7	3.9	V		
Clear voltage	VSDH		3.95	4.15	4.35	V		
Hysteresis	ΔVSD		0.3	0.45	0.6	V		
Output Block			•	•				
Output voltage 1-1	V _{OUT} 1-1	Low level I _O = 400μA		0.2	0.5	V		
Output voltage 1-2	V _{OUT} 1-2	Low level I _O = 10mA		0.9	1.2	V		
Output voltage 2	V _{OUT} 2	High level I _O = -20mA	V _{CC} -1.1	V _{CC} -0.9		V		
Output leakage current	l _O leak				10	μΑ		
Hall Amplifier Block			•	•				
Input bias current	IHB (HA)		-2	-0.5		μΑ		
Common-mode input voltage range 1	VICM1	When a Hall effect sensor is used	0.5		V _{CC} -2.0	V		
Common-mode input voltage range 2	VICM2	For single-sided input bias	0		V _{CC}	V		
		(Hall IC application)						
Hall input sensitivity			80			mVp-p		
Hysteresis	ΔV _{IN} (HA)		15	24	40	mV		
Input voltage low → high	VSLH (HA)		5	12	20	mV		
Input voltage high \rightarrow low	VSHL (HA)		-20	-12	-5	mV		
PWM Oscillator (PWM pin)								
High-level output voltage	V _{OH} (PWM)		2.75	3.0	3.25	V		
Low-level output voltage	V _{OL} (PWM)		1.2	1.35	1.5	V		
External capacitor charge current	ICHG	VPWM = 2.1V	-120	-90	-65	μΑ		
Oscillator frequency	f (PWM)	C = 2000pF		22		kHz		
Amplitude	V (PWM)		1.4	1.6	1.9	Vp-p		

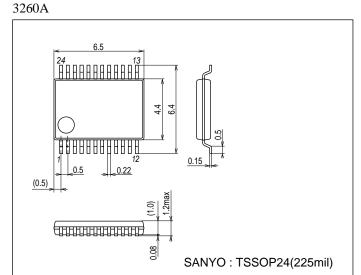
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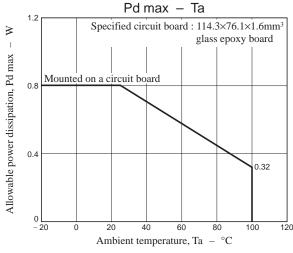
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Parameter	Symbol	Conditions	Ratings			Unit
raianietei	Symbol	Conditions	min	typ	max	Unit
El+ pin						
Input bias current	IB (CTL)		-1		1	μΑ
Common-mode input voltage range	VICM		0		VREG-1.7	V
Input voltage 1	VCTL1	Output duty 100%		3.0		V
Input voltage 2	VCTL2	Output duty 0%		1.35		V
Input voltage 1L	VCTL1L	Design target value. When VREG = 4.7V, 100%		2.82		V
Input voltage 2L	VCTL2L	Design target value. When VREG = 4.7V, 0%		1.29		V
Input voltage 1H	VCTL1H	Design target value. When VREG = 5.3V, 100%		3.18		V
Input voltage 2H	VCTL2H	Design target value. When VREG = 5.3V, 0%		1.44		V
HP pin						
Output saturation voltage	VHPL	I _O = 10mA		0.2	0.5	V
Output leakage current	IHPleak	V _O = 18V			10	μΑ
CSD oscillator (CSD pin)						
High-level output voltage	V _{OH} (CSD)		2.7	3.0	3.3	V
Low-level output voltage	V _{OL} (CSD)		0.7	1.0	1.3	V
External capacitor charge current	ICHG1	VCSD = 2V	-3.15	-2.5	-1.85	μΑ
External capacitor discharge current	ICHG2	VCSD = 2V	0.1	0.14	0.18	μА
Charge/discharge current ratio	RCSD	Charge current /discharge current	15	18	21	Times
RD pin					'	
Low-level output voltage	VRDL	I _O = 10mA		0.2	0.5	V
Output leakage current	IL (RD)	V _O = 18V			10	μΑ
Current limiter circuit (RF pin)	•		L L		l l	
Limiter voltage	VRF	RF-GND	0.225	0.25	0.275	V
PWMIN pin		1			<u> </u>	
Input frequency	f (PI)				50	kHz
High-level input voltage	V _{IH} (PI)		2.0		VREG	V
Low-level input voltage	V _{IL} (PI)		0		1.0	V
Input open voltage	V _{IO} (PI)		VREG-0.5		VREG	V
Hysteresis	V _{IS} (PI)		0.2	0.25	0.4	V
High-level input current	I _{IH} (PI)	VPWMIN = VREG	-10	0	10	μА
Low-level input current	I _{IL} (PI)	VPWMIN = 0V	-130	-90		μΑ
F/R pin	1		L		1	
High-level input voltage	V _{IH} (FR)		2.0		VREG	V
Low-level input voltage	V _{IL} (FR)		0		1.0	V
Input open voltage	V _{IO} (FR)		VREG-0.5		VREG	V
Hysteresis	V _{IS} (FR)		0.2	0.25	0.4	V
High-level input current	I _{IH} (FR)		-10	0	10	μА
Low-level input current	I _{IL} (FR)		-130	-90		<u>.</u> μΑ
N1 pin	, . <u>-</u>	ı	<u>l</u>		1	•
High-level input voltage	V _{IH} (N1)		2.0		VREG	V
Low-level input voltage	V _{IL} (N1)		0		1.0	V
Input open voltage	V _{IO} (N1)		VREG-0.5		VREG	V
High-level input current	I _{IH} (N1)	VN1 = VREG	-10	0	10	μA
Low-level input current	I _{IL} (N1)	VN1 = 0V	-130	-100	'	μΑ

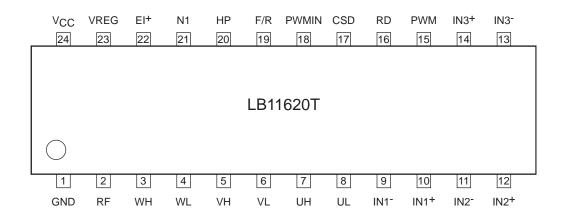
Package Dimensions

unit: mm (typ)





Pin Assignment



• Three-Phase Logic Truth Table (IN = "H" indicates the state where IN $^+$ > IN $^-$)

	F/R = "L"			F/R="H"			Output	
	IN1	IN2	IN3	IN1	IN2	IN3	PWM	
1	Н	L	Н	L	Н	L	VH	UL
2	Н	L	L	L	Н	Н	WH	UL
3	Н	Н	L	L	L	Н	WH	VL
4	L	Н	L	Н	L	Н	UH	VL
5	L	Н	Н	Н	L	L	UH	WL
6	L	L	Н	Н	Н	L	VH	WL

• PWMIN pin

2 ((1)211 (pin					
Input state	State				
High or open	Output off				
Low	Output on				

If the PWM pin is not used, the input must be held at the low level.

• N1 pin

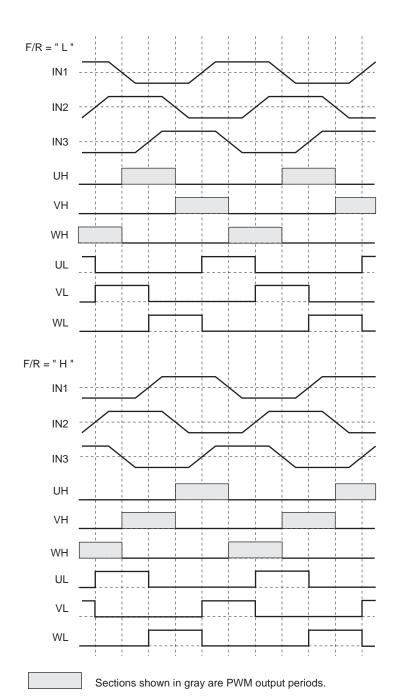
Input state	HP output	
High or open	Three Hall sensor synthesized output	
Low	Single Hall sensor output	

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Pin Functions

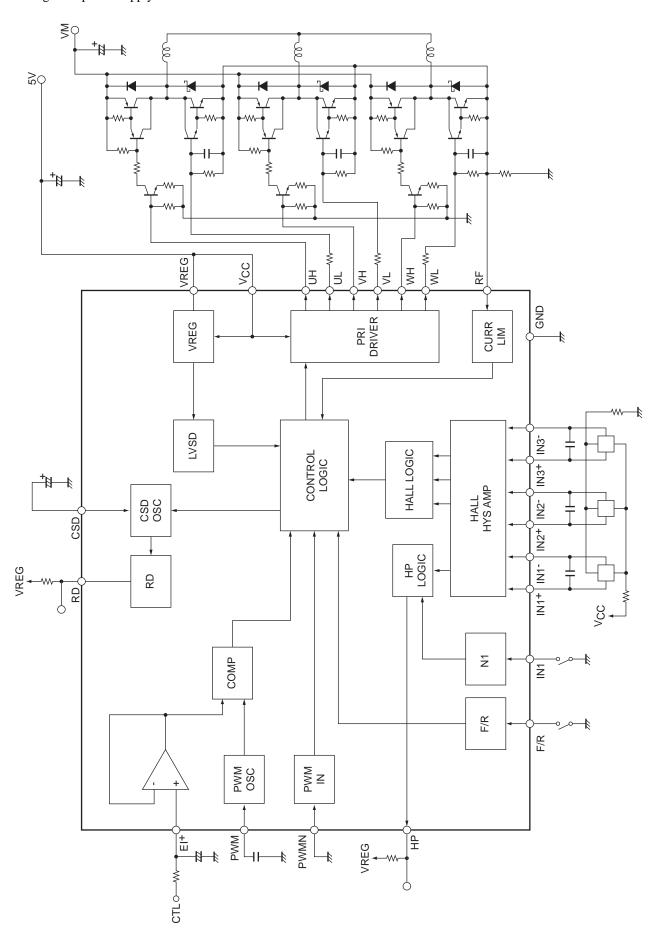
Pin No.	Pin	Description
1	GND	Ground
2	RF	Output current detection. The current detection resistor (Rf) voltage is sensed by the RF pin to implement current detection. The maximum output current is set by RF to be IOUT = 0.25/Rf.
7	UH	Outputs (PWM outputs).
5	VH	These are push-pull outputs.
3	WH	
8	UL	Outputs
6	VL	These are push-pull outputs.
4	WL	
10, 9	IN1+, IN1-	Hall sensor inputs from each motor phase.
12, 11	IN2+, IN2-	The logic high state indicates that IN ⁺ > IN ⁻ .
14, 13	IN3+, IN3-	If inputs are provided by a Hall effect sensor IC, the common-mode input range is expanded by biasing either the + or - input.
15	PWM	Functions as both the PWM oscillator frequency setting pin and the initial reset pulse setting pin. Connect a capacitor between this pin and ground.
16	RD	Lock (motor constrained) detection state output. This output is turned on when the motor is turning and off when the lock protection function detects that the motor has been stopped. This is an open collector output.
17	CSD	Sets the operating time for the lock protection circuit. Connect a capacitor between this pin and ground. Connect this pin to ground if the lock protection function is not used.
18	PWMIN	PWM pulse signal input. The output goes to the drive state when this pin is low, and to the off state when this pin is high or open. To use this pin for control, a CTL amplifier input such that the TOC pin voltage goes to the 100% duty state must be provided.
19	F/R	Forward/reverse control input
20	HP	Hall signal output (HP output). This provides either a single Hall sensor output or a synthesized 3-sensor output.
21	N1	Hall signal output (HP output) selection
22	EI+	CTL amplifier + (noninverting) input. The PWMIN pin must be held at the low level to use this input for motor control
23	VREG	5V regulator output (Used as the control circuit power supply. A low-voltage protection circuit is built in.) Connect a capacitor between this pin and ground for stabilization.
24	VCC	Power supply. Connect a capacitor between this pin and ground to prevent noise and other disturbances from affecting this IC.

Hall Sensor Signal Input/Output Timing Chart



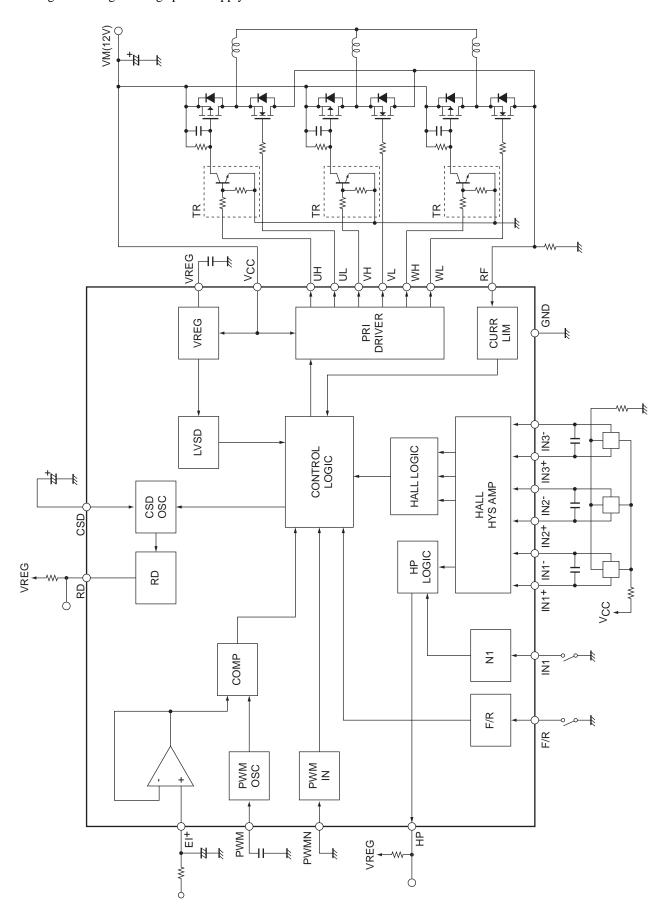
Block Diagram and Application Example 1

Bipolar transistor drive (high side PWM) using a 5V power supply



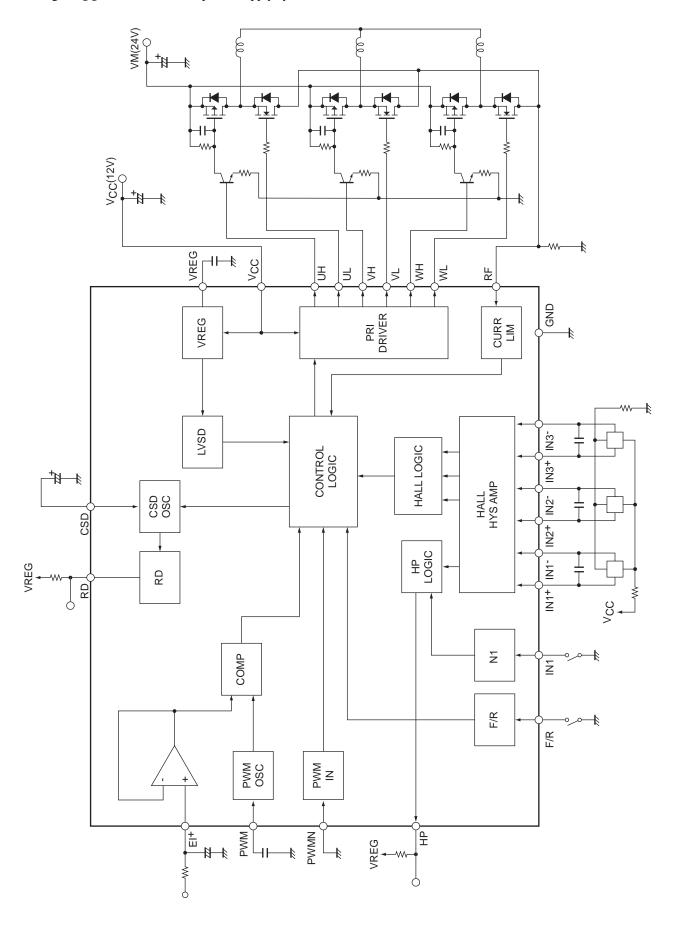
Application Example 2

54 MOS transistor drive (low side PWM) using a 12V single-voltage power supply



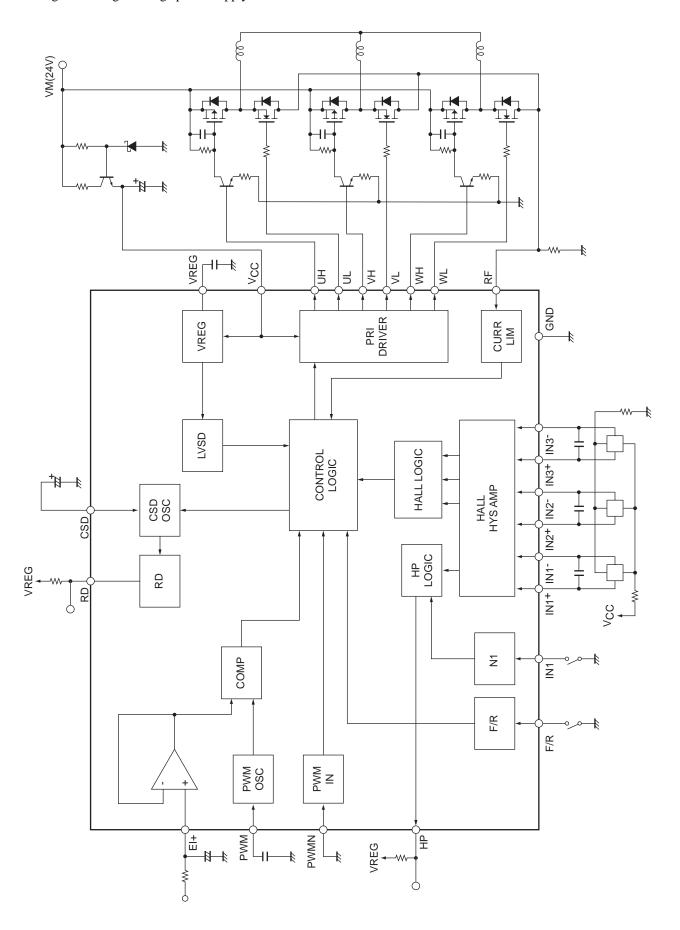
Application Example 3

MOS transistor drive (low side PWM) using a V_{CC} = 12V, VM = 24V power supply system



Application Example 4

MOS transistor drive (low side PWM) using a 24V single-voltage power supply



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